Supplementary Information

Ammonium phosphomolybdate: A Material for Dielectric Crossover and Non-Volatile Resistive Switching Performances

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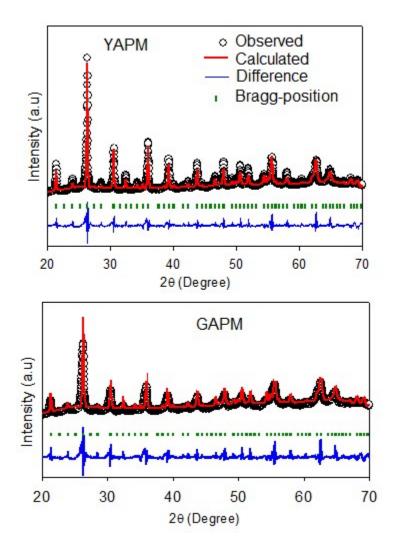


Figure S1. Rietveld refinement plots of YAPM and GAPM materials.

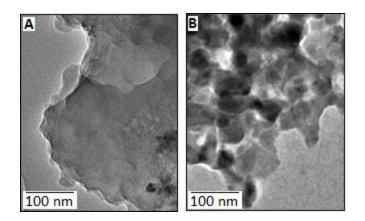


Figure S2. Transmission Electron Microscopy (TEM) images of YAPM (A) and GAPM (B)

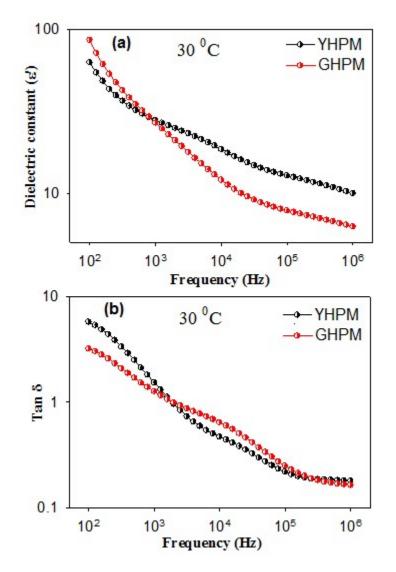


Figure S3. Room temperature (a) dielectric constant (ϵ') and (b) dielectric loss tangent (tan δ) curves of YHPM and GHPM materials.

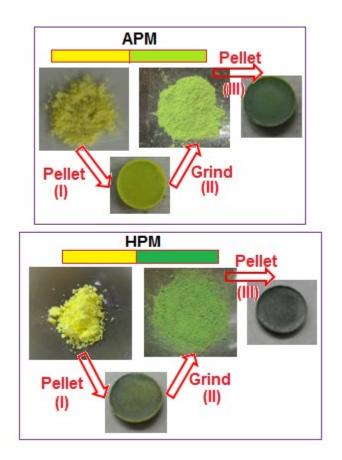


Figure S4. Pressure effect color changes (yellow to green) in APM and HPM materials.

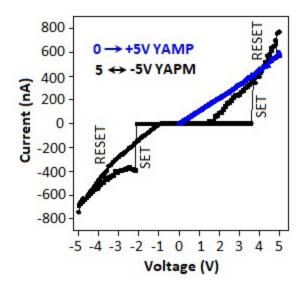


Figure S5. The current-voltage performance of the fabricated AulYAPMIAu device plotted on a linear scale.

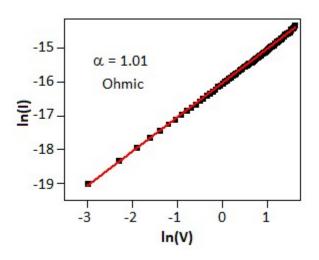


Figure S6. Current-voltage performance in forward bias (0 to 5V) condition of the fabricated AulYAPMIAu device exhibited ohmic (slope ~1.01) type of conduction process.